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	3	4	4	6	6	0	3	5/69	Loiacono			<u> </u>		
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SWL	Gh	Ghandhi, S. VLSI Fabrication Principles, John Wiley, 1983 pp 86-90, 98-100												
5WL	Sze	Sze, S., Physics of Semiconductor Devices, John Wiley, 1981, p 33												
SWC	IEEE Transactions on Electron Devices, vo. ED-31, No. 8, Aug. 1984, pp 1057, para 4 5; New York, US; S. Miyazawa													
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FORM PTO-1449 U.S. Department of Commerce ATTY. DOCKET NO. SERIAL NO: (Rev. 4/92) Patent and Trademark Office 501.22642CC9 INFORMATION DISCLOSURE **APPLICANT** STATEMENT BY APPLICANT **FUJISAKI FILING DATE GROUP** (Use several sheets if necessary) July 23, 2003 **U.S. PATENT DOCUMENTS EXAMINER** FILING DATE INITIAL DOCUMENT NUMBER DATE NAME CLASS **SUBCLASS** IF APPROPRIATE 3 5 Kawasaki 4 8 6 5 4 9/89 Fujisaki et al 5 3 0 8 6/98 6 2 9 4 8 0 9/01 Fujisaki et al YES NO OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Journal of Crystal Growth, Vol. 63 no. 2, Oct. 1983 pp 415-418, Amsterdam NL; Fornari Swc "Dislocation-free silicon-doped gallium arsenide grown by LEC Procedure Terashima "Control of Growth Parameters for Obtaining Highly Uniform Large Diameter LEC GaAs" 5th Conf. On Semi-insulating III-V Materials, 1988 pp 413-422 Matsuoko et al "uniformity Evaluation of MESFETs for FGaAs LSI Fabrication" IEEE Trans. On Elec. Dev. Vol ED31, no. 8 Aug. 1984 pp 1062 Applied Physics Letters, vol 44, no. 1, Jan. 1984 pp 74-76 New York, US; Hunter "Carbon in Semi-Insulating, liquid Encapsulated Czochralski GaAs" Patent Abstracts of Japan, vol. 4,no. 173 (C-32) [655], 29 Nov. 1980; JP A-55-113-669 Swo Sumitomo 2-09-1980 **DATE CONSIDERED EXAMINER** CRANE 6/2004 EXAMINER: Initial if citation is considered, draw line through citation if not in conformance and not considered. Include opy of this form with n xt communication to applicant. (Form PTO-1449 [6-4])